

Amendments to the Specification:

Please replace paragraph [0009] with the following amended paragraph [0009]:

[0009] For successful ALD processing, precursor gases are typically delivered to the reaction chamber at temperatures in excess of 100°C and often between 200°C and 300°C, particularly the varieties of precursor materials used for forming thin films on semiconductor substrates. With a conventional diaphragm valve, a significant amount of heat is conducted from the flow path through the valve, where it dissipates to the surrounding environment. Heat dissipation through the valve can result in cooling of the flow path and the associated condensation problems discussed above. To avoid condensation, the flow path may be heated, as described, for instance, in U.S. Provisional Patent Application No. 60/410,067 filed September 11, 2002, titled “Precursor Material Delivery System for Atomic Layer Deposition,” which is owned by the assignee of the present invention and incorporated herein by reference. However, heating the flow path may tend to contribute to overheating of the actuators in conventional diaphragm valves. The present inventors have recognized a need for an improved diaphragm valve in which the valve passage, diaphragm, and valve seat can be kept hot enough to prevent the precursor vapor from condensing (typically in the range of 130°C to 260°C or hotter), without overheating the valve actuator.